

# SANYO Semiconductors DATA SHEET

# 2SB1664 — PNP Epitaxial Planar Silicon Darlington Transistor Driver Applications

# **Applications**

· Motor drivers, printer hammer drivers, relay drivers, voltage regulator control.

#### **Features**

- · High DC current gain.
- · Large current capacity and wide ASO.
- · Low saturation voltage.

# **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

| Parameter                    | Symbol | Conditions | Ratings     | Unit |
|------------------------------|--------|------------|-------------|------|
| Collector-to-Base Voltage    | VCBO   |            | -110        | V    |
| Collector-to-Emitter Voltage | VCEO   |            | -100        | V    |
| Emitter-to-Base Voltage      | VEBO   |            | -6          | V    |
| Collector Current            | IC     |            | -8          | Α    |
| Collector Current (Pulse)    | ICP    |            | -12         | Α    |
| Collector Dissipation        | PC     | Tc=25°C    | 35          | W    |
| Junction Temperature         | Tj     |            | 150         | °C   |
| Storage Temperature          | Tstg   |            | -55 to +150 | °C   |

#### Electrical Characteristics at Ta=25°C

| Parameter                               | Symbol           | Conditions                                |      | Ratings |      |      |
|---|------------------|---|------|---------|------|------|
|   |                  |   | min  | typ     | max  | Unit |
| Collector Cutoff Current                | ICBO             | V <sub>CB</sub> =-80V, I <sub>E</sub> =0A |      |         | -0.1 | mA   |
| Emitter Cutoff Current                  | IEBO             | V <sub>EB</sub> =-5V, I <sub>C</sub> =0A  |      |         | -3.0 | mA   |
| DC Current Gain                         | hFE              | VCE=-3V, IC=-4A                           | 1500 | 4000    |      |      |
| Gain-Bandwidth Product                  | fŢ               | V <sub>CE</sub> =-5V, I <sub>C</sub> =-4A |      | 20      |      | MHz  |
| Collector-to-Emitter Saturation Voltage | VCE(sat)         | IC=-4A, IB=-8mA                           |      | -1.0    | -1.5 | V    |
| Base-to-Emitter Saturation Voltage      | VBE(sat)         | IC=-4A, IB=-8mA                           |      |         | -2.0 | V    |
| Collector-to-Base Breakdown Voltage     | V(BR)CBO         | IC=-5mA, IE=0A                            | -110 |         |      | V    |
| Collector-to-Emitter Breakdown Voltage  | V(BR)CEO         | IC=-50mA, RBE=∞                           | -100 |         |      | V    |
| Turn-ON Time                            | ton              | See specified Test Circuit.               |      | 0.7     |      | μs   |
| Storage Time                            | t <sub>stg</sub> | See specified Test Circuit.               |      | 1.4     |      | μs   |
| Fall Time                               | tf               | See specified Test Circuit.               |      | 1.5     |      | μs   |

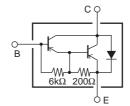
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## **Package Dimensions**

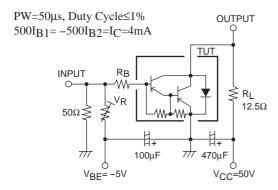
unit : mm (typ) 7002-003

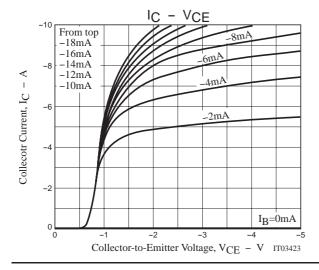
# 8.2 7.8 6.2 3 1.1 Base 2.2 Emitter 3. Collector SANYO: ZP

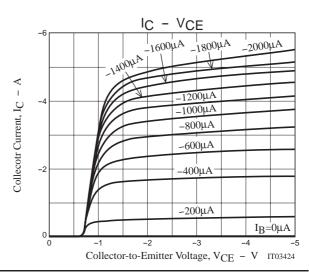
## **Electrical Connection**

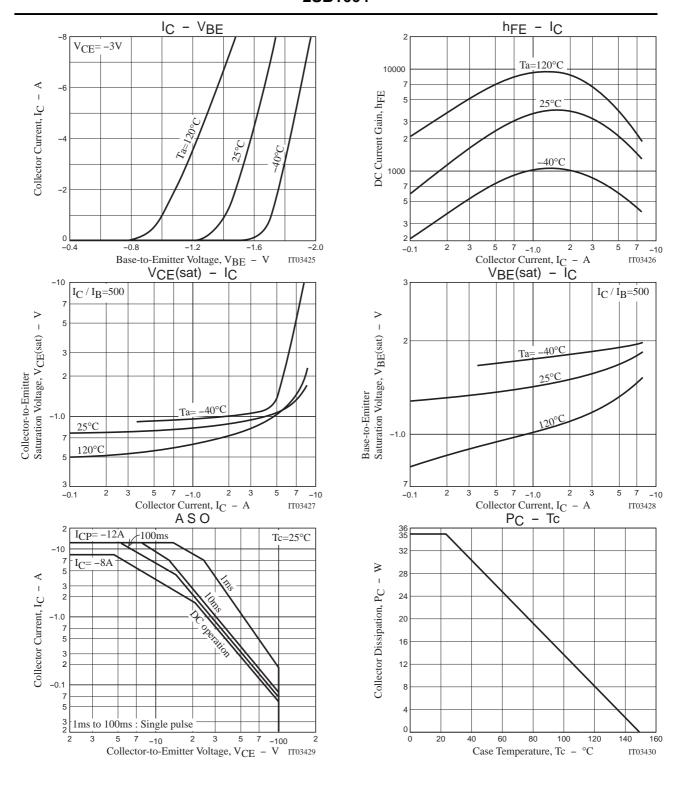


## **Switching Time Test Circuit**









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